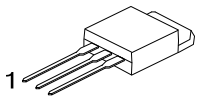
60V, 30A N-CHANNEL POWER MOSFET



TO-251

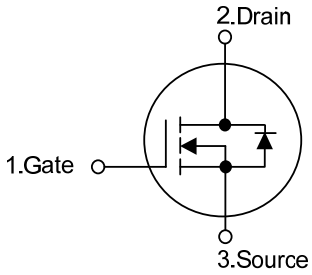
■ DESCRIPTION

The UTC **30N06V-Q** is a low voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and excellent avalanche characteristics. This power MOSFET is usually used at automotive applications in power supplies, high efficient DC to DC converters and battery operated products.

■ FEATURES

* $R_{DS(ON)}$ < 40mΩ@V_{GS} = 10 V, I_D=15A
* Fast switching capability
* Avalanche energy specified

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
30N06VL-TM3-T	30N06VG-TM3-T	TO-251	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

30N06VL-TM3-T (1)Packing Type (2)Package Type (3)Lead Free	(1) T: Tube (2) TM3: TO-251 (3) L: Lead Free, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS(T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate to Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	T_C = 25°C	I_D	30	A
	T_C = 100°C		21.3	A
Pulsed Drain Current (Note 2)		I_{DM}	120	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	250	mJ
	Repetitive (Note 2)	E_{AR}	8	mJ
Power Dissipation		P_D	46	W
Junction Temperature		T_J	+150	°C
Operation Temperature		T_{OPR}	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repeativity rating: pulse width limited by junction temperature
3. L=0.66mH, I_{AS}=30A, V_{DD}=25V, R_G=20Ω, Starting T_J=25°C

■ THERMAL DATA

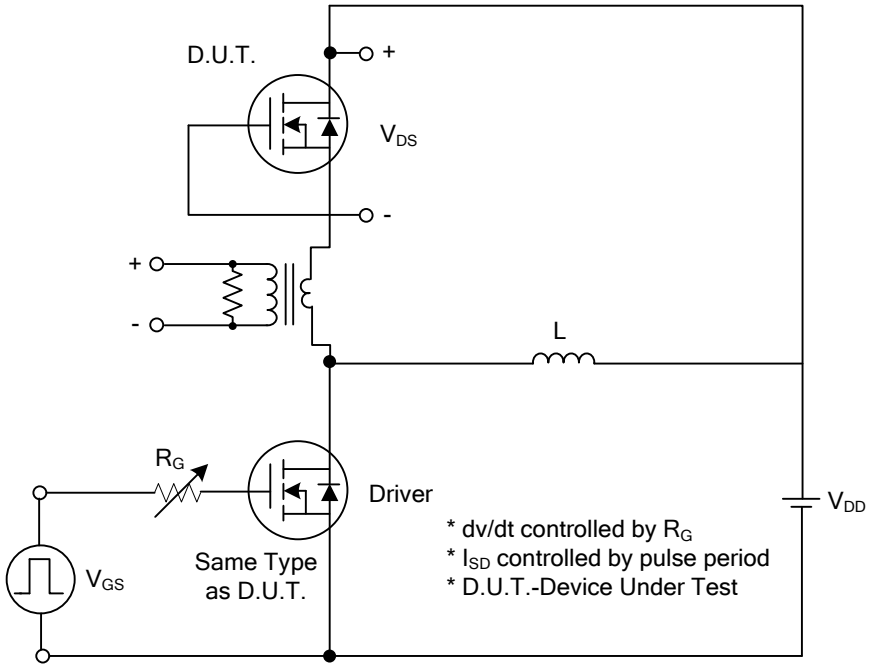
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	2.85	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C = 25°C, unless otherwise specified)

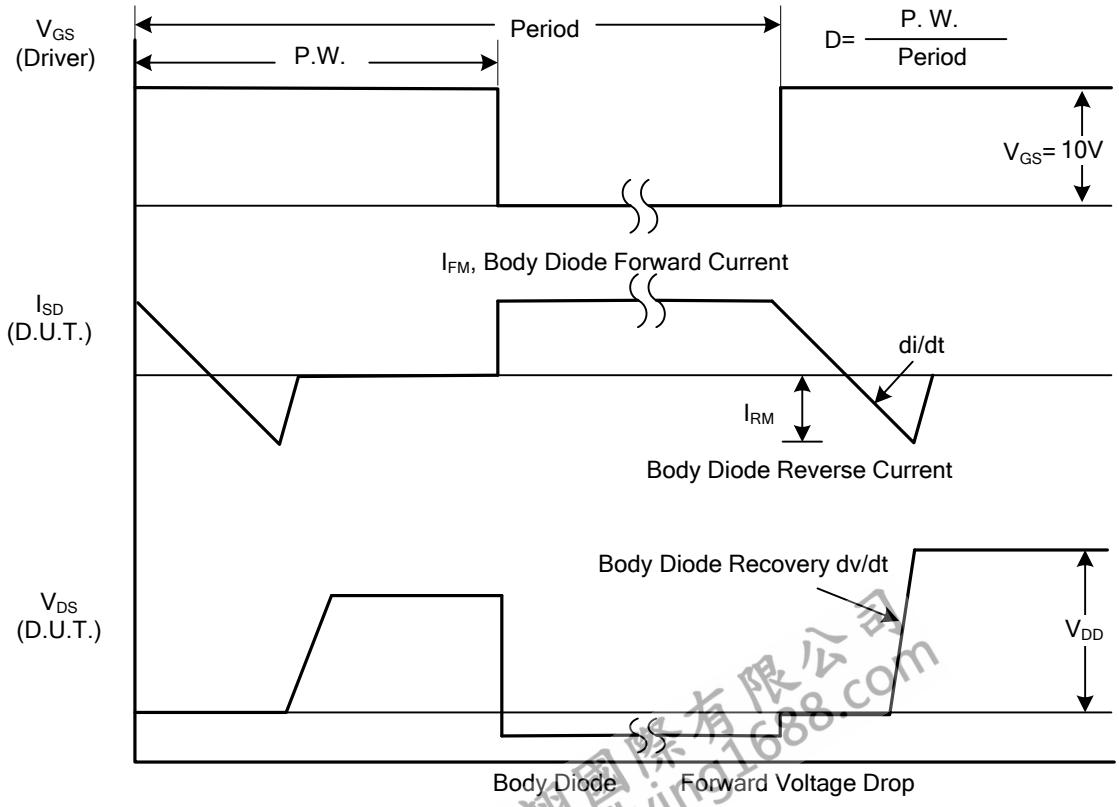
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS} = 0 V, I_D = 250 μA	60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} = 20V, V_{DS} = 0 V			100	nA
	Reverse		V_{GS} = -20V, V_{DS} = 0 V			-100	nA
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D =250μA, Referenced to 25°C		0.06		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.6		2.4	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 15 A			40	mΩ
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1MHz		800		pF
Output Capacitance		C_{OSS}			300		pF
Reverse Transfer Capacitance		C_{RSS}			50		pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} = 30V, I_D =15 A, V_{GS}=10V (Note 1, 2)		30		ns
Turn-On Rise Time		t_R			50		ns
Turn-Off Delay Time		$t_{D(OFF)}$			280		ns
Turn-Off Fall Time		t_F			120		ns
Total Gate Charge		Q_G	V_{DS} = 60V, V_{GS} = 10 V, I_D = 24A (Note 1, 2)		30		nC
Gate-Source Charge		Q_{GS}			5		nC
Gate-Drain Charge		Q_{GD}			8		nC
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 30A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S				30	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				120	A

Notes: 1. Pulse Test : Pulse width ≤300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

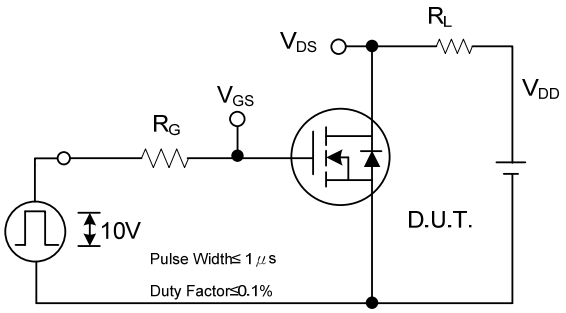


Peak Diode Recovery dv/dt Test Circuit

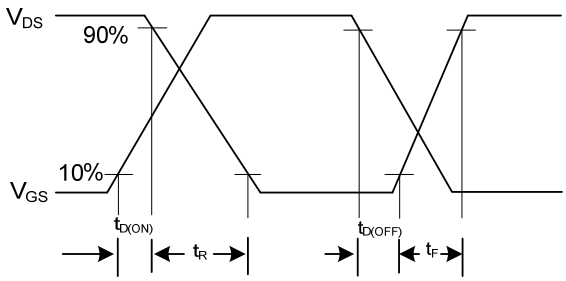


Peak Diode Recovery dv/dt Waveforms

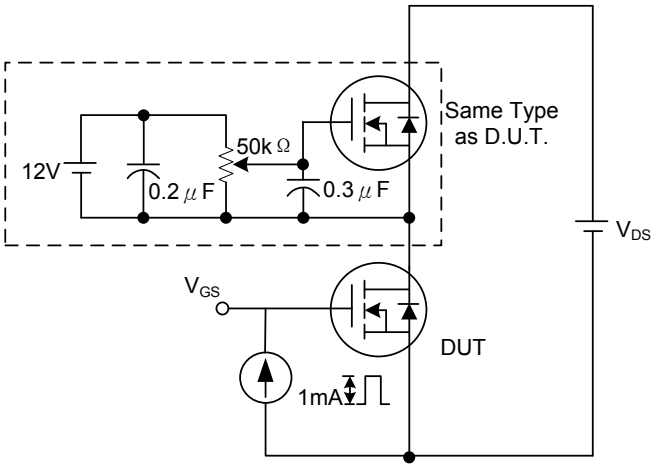
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



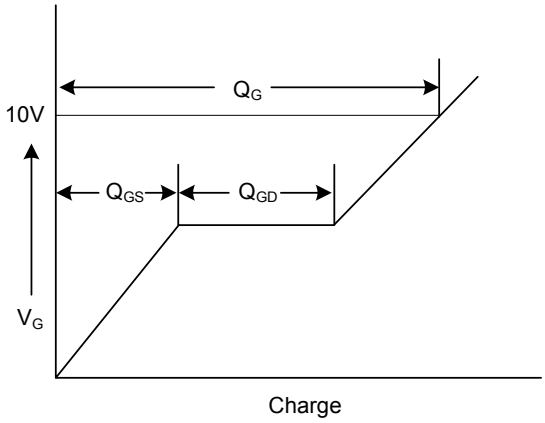
Switching Test Circuit



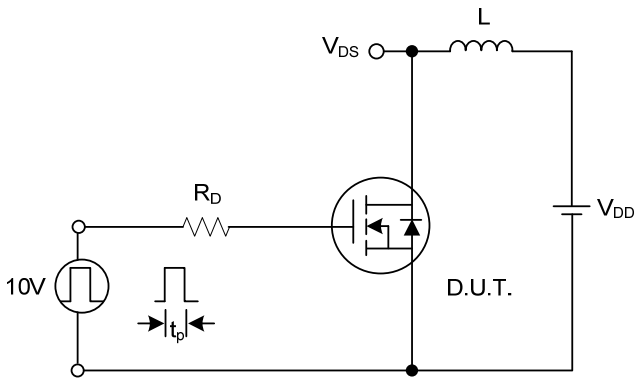
Switching Waveforms



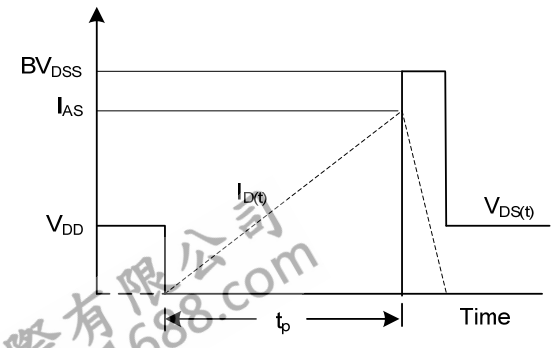
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms